MBD301G, MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G

Silicon Hot-Carrier Diodes

Schottky Barrier Diodes

These devices are designed primarily for high-efficiency UHF and VHF detector applications. They are readily adaptable to many other fast switching RF and digital applications. They are supplied in an inexpensive plastic package for low-cost, high-volume consumer and industrial/commercial requirements. They are also available in a Surface Mount package.

Features

- Extremely Low Minority Carrier Lifetime 15 ps (Typ)
- Very Low Capacitance 1.5 pF (Max) @ V_R = 15 V
- Low Reverse Leakage I_R = 13 nAdc (Typ) MBD301, MMBD301
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Forward Current (DC)	ΙF	200 (Max)	mA
Total Device Dissipation (a) T _A = 25°C MBD301G MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G Derate above 25°C MBD301G MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G	P _F	280 200 2.8 2.0	MW mW/°C
Operating Junction Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

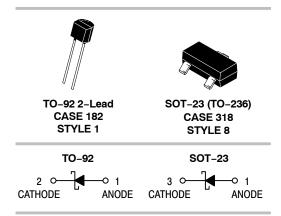
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



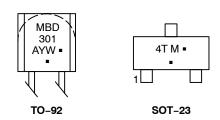
ON Semiconductor®

www.onsemi.com

30 VOLTS SILICON HOT-CARRIER DETECTOR AND SWITCHING DIODES



MARKING DIAGRAMS



A = Assembly Location

/ = Year

W = Work Week

4T = Device Code (SOT-23)

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MBD301G, MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μA)	V _{(BR)R}	30	-	-	V
Total Capacitance (V _R = 15 V, f = 1.0 MHz) Figure 1	C _T	-	0.9	1.5	pF
Reverse Leakage (V _R = 25 V) Figure 3	I _R	-	13	200	nAdc
Forward Voltage (I _F = 1.0 mAdc) Figure 4	V _F	-	0.38	0.45	Vdc
Forward Voltage (I _F = 10 mAdc) Figure 4	V _F	-	0.52	0.6	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]
MBD301G	TO-92 (Pb-Free)	5,000 Units / Bulk
MMBD301LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD301LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBD301LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MBD301G, MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G

TYPICAL ELECTRICAL CHARACTERISTICS

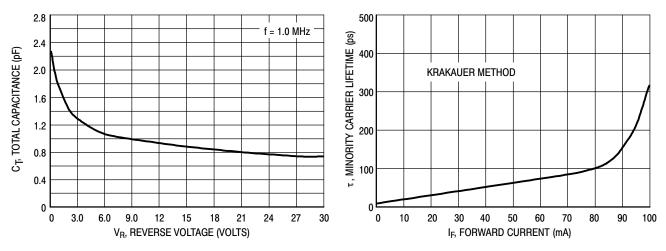


Figure 1. Total Capacitance

Figure 2. Minority Carrier Lifetime

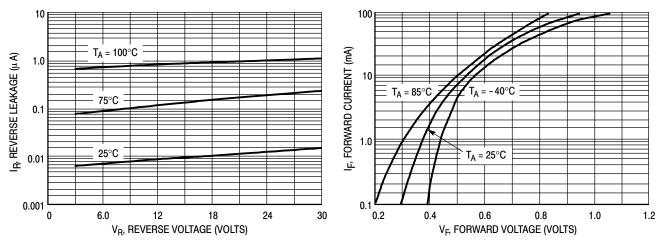


Figure 3. Reverse Leakage

Figure 4. Forward Voltage

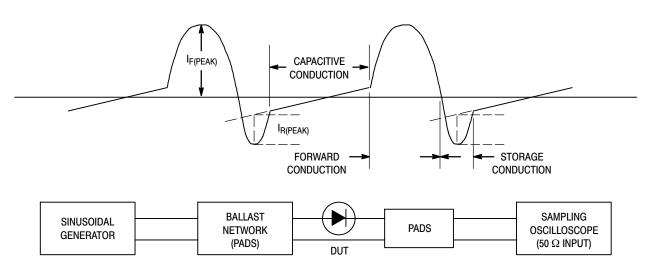


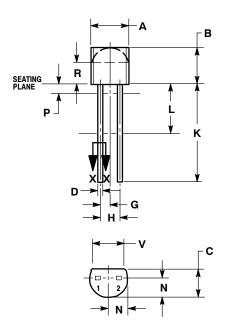
Figure 5. Krakauer Method of Measuring Lifetime



TO-92 (TO-226) CASE 182-06 **ISSUE L**

DATE 04/18/1998







SECTION X-X

- OTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND ZONE R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND

- BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.21	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.050	BSC	1.27 BSC		
Н	0.100	BSC	2.54 BSC		
ſ	0.014	0.016	0.36	0.41	
K	0.500	-	12.70		
٦	0.250		6.35		
N	0.080	0.105	2.03	2.66	
Р		0.050		1.27	
R	0.115	-	2.93		
٧	0.135		3.43		

STYLE 1: PIN 1. ANODE 2. CATHODE STYLE 2: PIN 1. CATHODE 2. ANODE

STYLE 3: PIN 1. MAIN TERMINAL 1 2. MAIN TERMINAL 2 STYLE 4: CANCELLED STYLE 5: PIN 1. INPUT 2. OUTPUT

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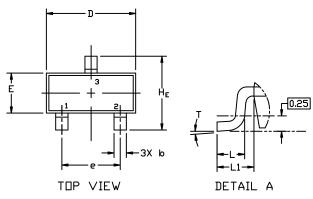


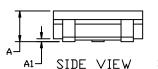


SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: N PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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